L	Hits	Search Text	DB	mimo atama
Number		Journal Text	מע	Time stamp
-	50909	substrate and (crystalline or (single adj	USPAT	2001/10/29
		crystalline) or single-crystalline or	1	09:14
	}	monocrystalline or mono-crystalline)		
-	12606		USPAT	2001/10/29
		adj crystalline) or single-crystalline or		09:14
		monocrystalline or mono-crystalline))	ļ	
_	1784	and (mask or optical adj mask)		
_	1/84	((substrate and (crystalline or (single adj crystalline) or single-crystalline or	USPAT	2001/10/29
	ĺ	monocrystalline or mono-crystalline or		09:16
		and (mask or optical adj mask)) and		
		irradiat\$4 and (laser or lasers)	·	
_	1331	(((substrate and (crystalline or (single	USPAT	2001/10/29
		adj crystalline) or single-crystalline or		09:16
		monocrystalline or mono-crystalline))		
		and (mask or optical adj mask)) and		
		irradiat\$4 and (laser or lasers)) and		
_	523	(insulati\$4 or dielectric)	110000	2001/10/20
] 523	<pre>((((substrate and (crystalline or (single adj crystalline) or single-crystalline or</pre>	USPAT	2001/10/29
		monocrystalline or mono-crystalline))		09.24
		and (mask or optical adj mask)) and		
		irradiat\$4 and (laser or lasers)) and		
		(insulati\$4 or dielectric)) and		
		(alignment or (alignment adj mark))		
-	381	(((((substrate and (crystalline or	USPAT	2001/10/29
		(single adj crystalline) or		11:41
		single-crystalline or monocrystalline or		
		<pre>mono-crystalline)) and (mask or optical adj mask)) and irradiat\$4 and (laser or</pre>		
		lasers)) and (insulati\$4 or dielectric))		
		and (alignment or (alignment adj mark)))		
İ		and amorphous and crystalline		
-	1	("5821562").PN.	USPAT	2001/10/29
				11:41
-	1	(("5821562").PN.) and (mask same laser)	USPAT	2001/10/29
	_ ,	////5001560/// 2010		11:42
-	1	(("5821562").PN.) and mask and laser	USPAT	2001/10/29
				12:50

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L Number	Hits	Search Text	DB	Time stamp
-	44910	semiconductor adj substrate	USPAT	2001/10/19
-	85		USPAT	11:50 2001/10/18
-	37	, (= = = = = = = = = = aa, babbctacc, and	USPAT	13:48 2001/10/18
		(optical adj mask)) and (insualt\$3 or dielectric)		13:49
-	11	(optical adj mask)) and (insualt\$3 or	USPAT	2001/10/18 14:05
_	224	dielectric)) and (laser or lasers) ("438/697").CCLS.	USPAT	2001/10/18
-	26	(("438/697").CCLS.) and (laser or lasers)	USPAT	14:08 2001/10/18
_	1	((("438/697").CCLS.) and (laser or lasers)) and (optical adj mask)	USPAT	14:12 2001/10/18 14:15
-	1		USPAT	2001/10/18 14:16
-	1426	laser adj annealing	USPAT	2001/10/18
_	7	mask)	USPAT	2001/10/18
-	7	mask)) and (insulat\$3 or dielectric)	USPAT	2001/10/18 14:17
-	1486	(laser adj annealing) or (laser adj crystalliz\$4)	USPAT	2001/10/19 10:27
-	476	crystalliz\$4)) and alignment	USPAT	2001/10/19 10:29
_	419	(((laser adj annealing) or (laser adj crystalliz\$4)) and alignment) and (insulating or dielectric)	USPAT	2001/10/19 10:29
_	13	((((laser adj annealing) or (laser adj crystalliz\$4)) and alignment) and (insulating or dielectric)) and amorphous	USPAT	2001/10/19 10:30
		and (single adj crystalline) and (monocrystalline)		
-	1	("5643826").PN.	USPAT	2001/10/19 11:50
_	1	(("5643826").PN.) and laser	USPAT	2001/10/19 12:01
-	1	("5620910").PN.	USPAT	2001/10/19 12:01
_	1	(("5620910").PN.) and laser	USPAT	2001/10/19 12:01
_	1	((("5620910").PN.) and laser) and alignment	USPAT	2001/10/19 12:09
_	473	Crystal\$ and laser and (alignment adj mark)	USPAT	2001/10/19 12:14
-	23	(Crystal\$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)	USPAT	2001/10/19 12:15
_	0	((Crystal\$ and laser and (alignment adj mark)) and (amorphous adj silicon) and	USPAT	2001/10/19 12:15
-	0	(crystalline adj silicon)) and ((laser adj anneal) same mask) ((Crystal\$ and laser and (alignment adj mark)) and (amorphous adj silicon) and	USPAT	2001/10/19 12:15
-	0	<pre>(crystalline adj silicon)) and ((laser adj anneal) and mask) ((Crystal\$ and laser and (alignment adj mark)) and (amorphous adj silicon) and</pre>	USPAT	2001/10/19
-	o	(crystalline adj silicon)) and ((laser adj anneal) and (ARC or mask or resist)) ((Crystal\$ and laser and (alignment adj	USPAT	2001/10/19
		<pre>mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and (laser adj anneal)</pre>		12:16

-	5	((Crystal\$ and laser and (alignment adj mark)) and (amorphous adj silicon) and	USPAT	2001/10/24
		(crystalline adj silicon)) and (laser adj anneal\$)		11:02
-	5	((Crystal\$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and (laser adj anneal\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/10/24 11:03
-	5	((Crystal\$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and (laser adj anneal\$)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/10/24 11:07
-	4527	(thin adj film adj resistor\$2)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/24 11:08
-	94	<pre>((thin adj film adj resistor\$2)) and amorphous and ((single adj crystalline) or monocrystalline or single-crystalline or crystalline)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/24
-	16	(("5569610") or ("5543352") or ("0553416") or ("5531182") or ("5529937") or ("5508533") or ("5501989") or ("5488000") or ("54881121") or ("54037722") or ("5289030") or ("5278093") or ("5278093") or ("4309223") or ("4068020") or ("43783049")).PN.	USPAT	2001/10/24 11:40
-	466	("257/350").CCLS.	USPAT	2001/10/25 15:47
-	305	(("257/350").CCLS.) and ((laser adj anneal) or crystal\$ or irradiat\$4)	USPAT	2001/10/25
-	273	(("257/350").CCLS.) and (amorphous or (single-crystalline) or monocrystalline or (single adj crystalline) or crystalline)	USPAT	2001/10/25 15:52
-	104	((("257/350").CCLS.) and ((laser adj anneal) or crystal\$ or irradiat\$4)) and amorphous and (single-crystalline or monocrystalline or crystalline or (single adj crystalline))	USPAT	2001/10/25 16:11